

**PENDING CLAIMS**

The following is a list of currently pending claims. Claims 1 and 3-5 are cancelled. Please amend claims 2, 6, and 7 as shown below. Please add new claim 10.

1. (Cancelled)
2. (Currently amended) The semiconductor structure of claim ~~4~~ 6 wherein the first silicide layer comprises cobalt silicide.
- 3.-5. (Cancelled)
6. (Currently amended) A semiconductor structure comprising:  
a first silicide layer;  
a silicon dioxide layer on and in contact with the first silicide layer;  
a first lightly doped semiconductor layer on and in contact with the silicon dioxide layer; and  
a second heavily doped semiconductor layer on and in contact with the lightly doped semiconductor layer, wherein the silicon dioxide layer is an antifuse layer,  
wherein the antifuse layer is capable of being breached, wherein a diode is formed after the antifuse layer is breached, The semiconductor structure of claim ~~5~~  
wherein the diode is a Schottky diode.
7. (Currently amended) The semiconductor structure of claim ~~4~~ 6 wherein the structure is a portion of a first memory level.
8. (Original) The semiconductor structure of claim 7 wherein at least a second memory level exists above the first memory level.

9. (Original) The semiconductor structure of claim 8 wherein at least a second memory level exists below the first memory level.
10. (New) The semiconductor structure of claim 6 wherein the dopant type of the first lightly doped and second heavily doped semiconductor layers is the same.

**CLAIM AMENDMENTS: DISCUSSION**

Claims 1 and 3-5 have been cancelled. Claim 2 has been amended to depend from claim 6, rather than from cancelled claim 1, from which it formerly depended.

Claim 6 has been amended to include the limitations of cancelled claims 1, 3, 4, and 5 from which it formerly depended; thus the scope of this claim is unchanged. Claim 7 has been amended to depend from claim 6, rather than from cancelled claim 1, from which it formerly depended.

New claim 10 depends from claim 6 and includes the limitation that the dopant type of the first lightly doped and second heavily doped semiconductor layers is the same. Support for this amendment can be found, for example, in Fig. 5 of the present application.